

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	$I_D$
-30V	8mΩ@-10V	-65A
	12mΩ@-4.5V	

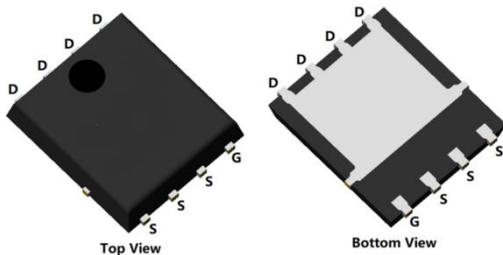
## Feature

- Trench Power LV MOSFET technology
- High density cell design for Low RDS(ON)
- High Speed switching
- Suffix "-Q1" for AEC-Q101

## Application

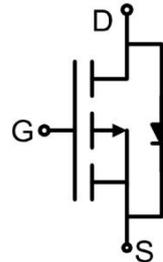
- Power management
- Battery protection
- Load switch

## Package

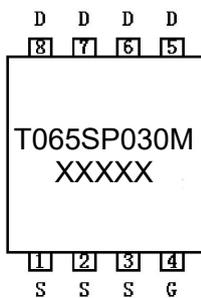


PDFN5\*6-8L

## Circuit diagram



## Marking



### Absolute maximum ratings (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current (T <sub>C</sub> =25°C)	I <sub>D</sub>	-65	A
Continuous Drain Current (T <sub>C</sub> =100°C)	I <sub>D</sub> (100°C)	-41	A
Pulsed Drain Current <sup>1)</sup>	I <sub>DM</sub>	-260	A
Single Pulse Avalanche Energy <sup>2)</sup>	E <sub>AS</sub>	256	mJ
Power Dissipation <sup>3)</sup> (T <sub>C</sub> =25°C)	P <sub>D</sub>	71	W
Thermal Resistance Junction to Case	R <sub>θJC</sub>	1.76	°C/W
Operating Junction Temperature	T <sub>J</sub>	-55 ~ +150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

### Electrical characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-30			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V			-1	μA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V			±100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-1	-1.5	-2.5	V
Drain-source on-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> = -32.5A		6	8	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -20A		9	12	
<b>Dynamic characteristics<sup>4)</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, f = 1MHz		2360		pF
Output Capacitance	C <sub>oss</sub>			370		
Reverse Transfer Capacitance	C <sub>rss</sub>			325		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V I <sub>D</sub> = -32.5A		48		nC
Gate-Source Charge	Q <sub>gs</sub>			12		
Gate-Drain Charge	Q <sub>gd</sub>			11		
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V I <sub>D</sub> = -32.5A, R <sub>G</sub> = 6Ω		17		nS
Turn-on rise time	t <sub>r</sub>			11		
Turn-off delay time	t <sub>d(off)</sub>			118		
Turn-off fall time	t <sub>f</sub>			59		
<b>Source-Drain Diode characteristics</b>						
Diode Forward Current	I <sub>S</sub>				-65	A
Diode Forward voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -32.5A			-1.2	V
Reverse Recovery Time	T <sub>rr</sub>	I <sub>F</sub> = -32.5A, di/dt = -100A/μs		22		nS
Reverse Recovery Charge	Q <sub>rr</sub>			49		nC

Notes:

- 1) Repetitive rating; pulse width limited by max. junction temperature.
- 2) T<sub>J</sub> = 25°C, V<sub>DD</sub> = -20V, V<sub>G</sub> = -10V, R<sub>G</sub> = 25Ω, L = 2mH, I<sub>AS</sub> = -16A.
- 3) P<sub>d</sub> is based on max. junction temperature, using junction-case and junction-ambient thermal resistance.
- 4) Guaranteed by design, not subject to production testing.

## Typical Characteristics

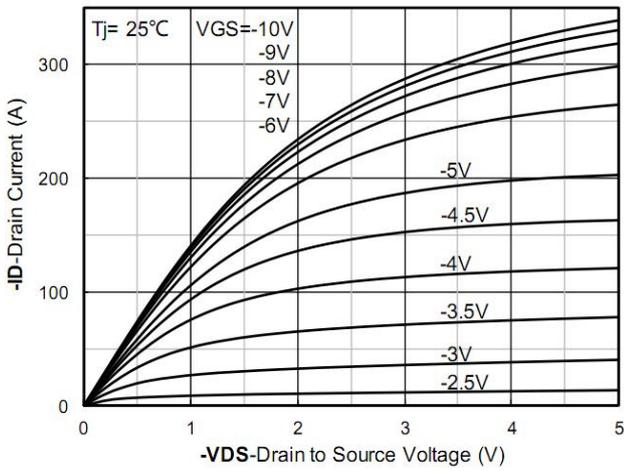


Figure 1. Output Characteristics

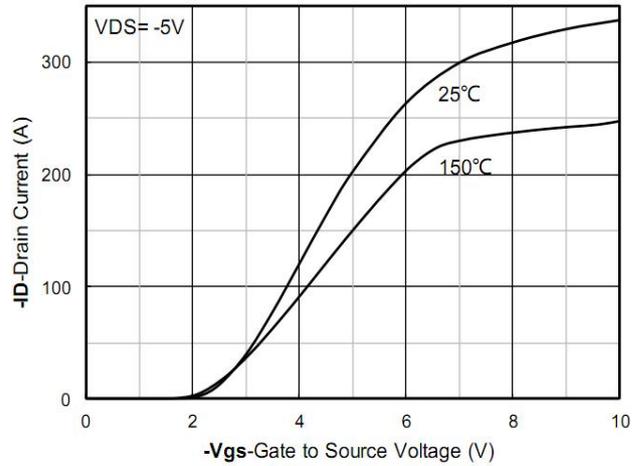


Figure 2. Transfer Characteristics

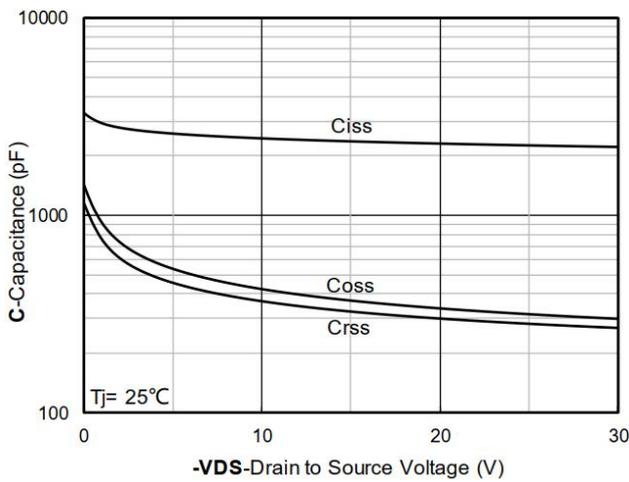


Figure 3. Capacitance Characteristics

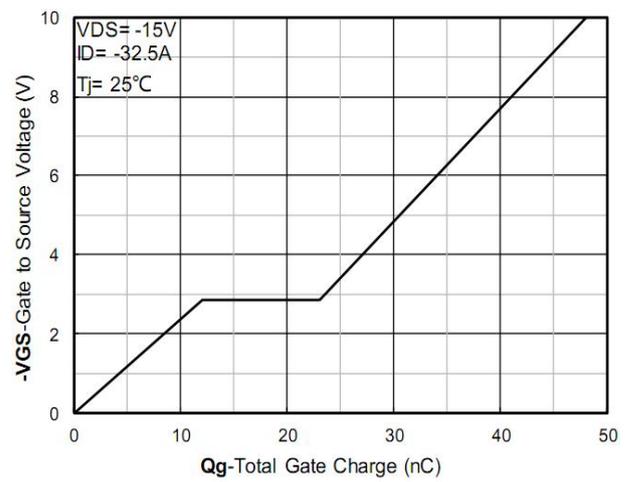


Figure 4. Gate Charge

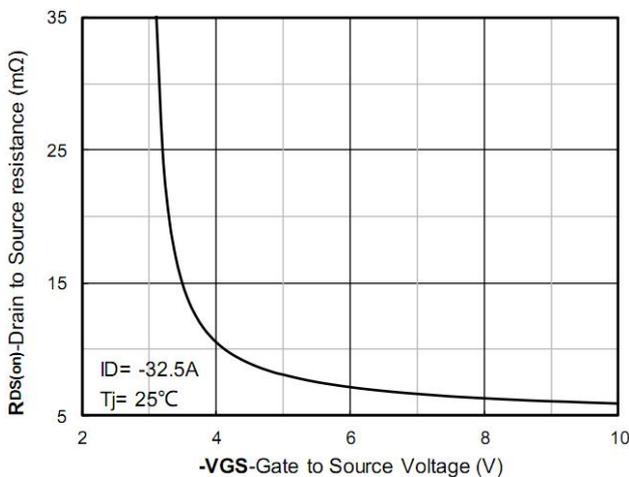


Figure 5. On-Resistance vs Gate to Source Voltage

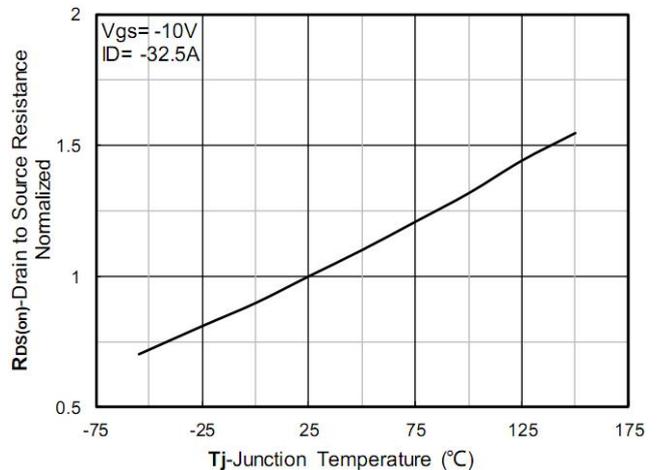


Figure 6. Normalized On-Resistance

## Typical Characteristics

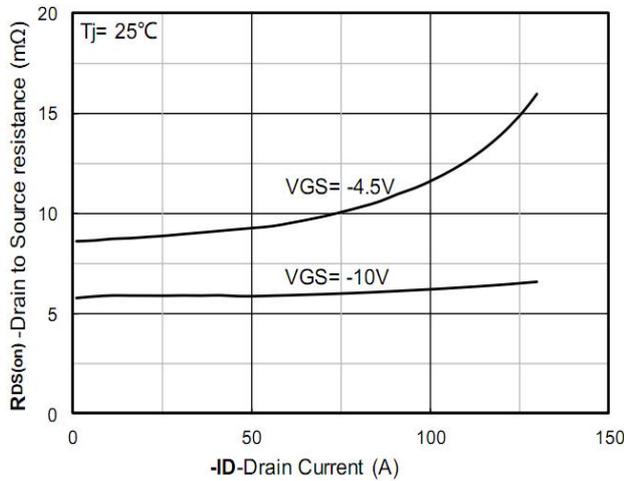


Figure 7.  $R_{DS(on)}$  VS Drain Current

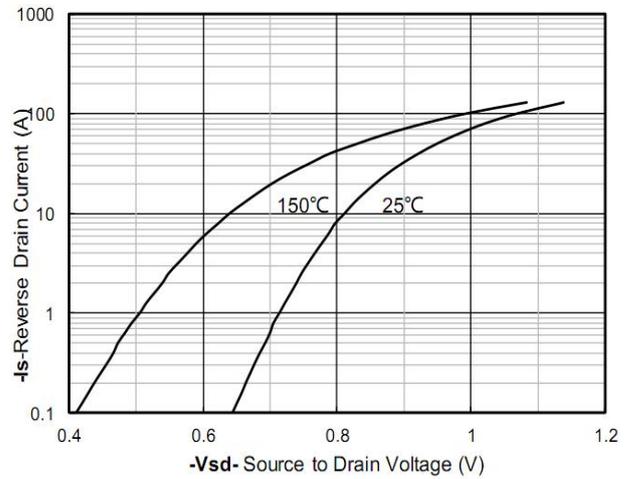


Figure 8. Forward characteristics of reverse diode

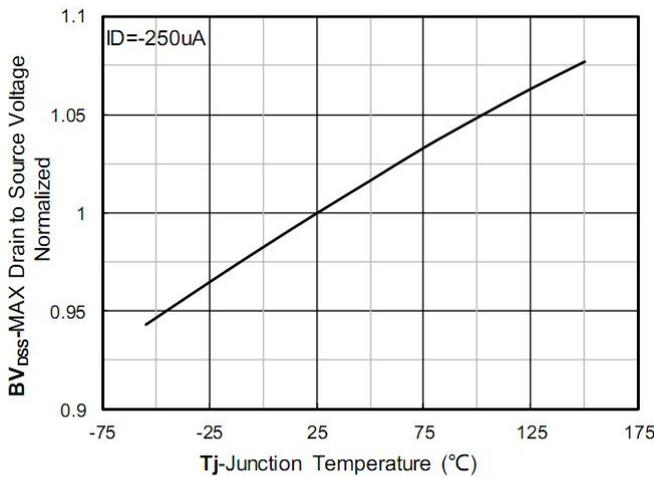


Figure 9. Normalized breakdown voltage

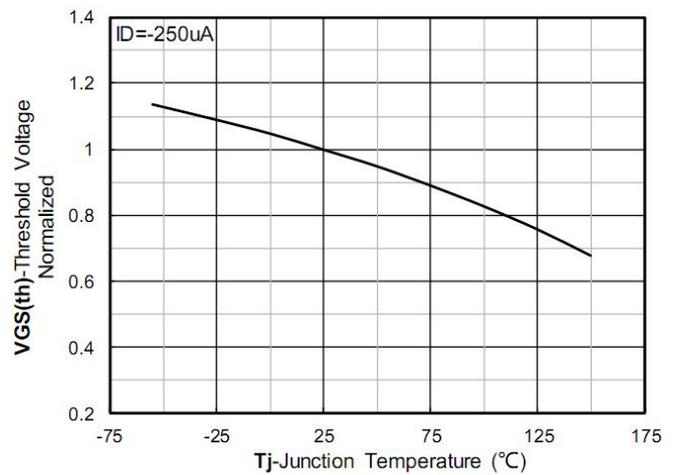


Figure 10. Normalized Threshold voltage

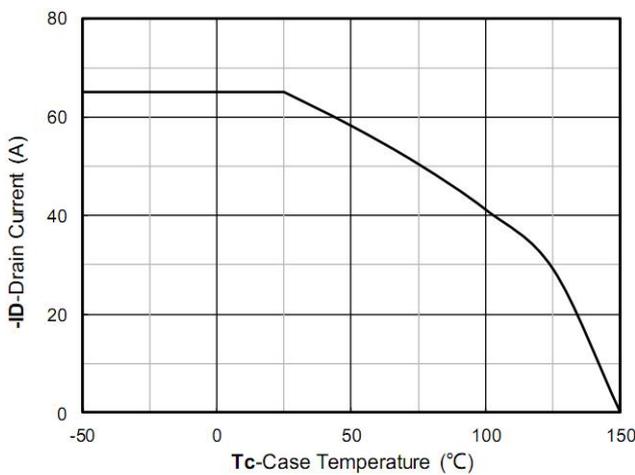


Figure 11. Current dissipation

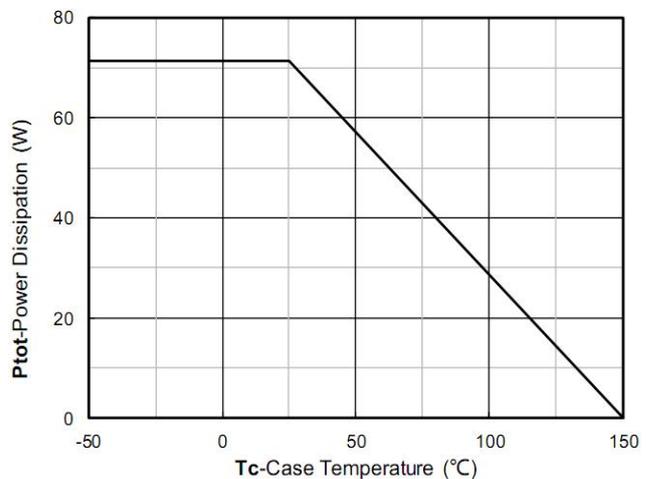


Figure 12. Power dissipation

## Typical Characteristics

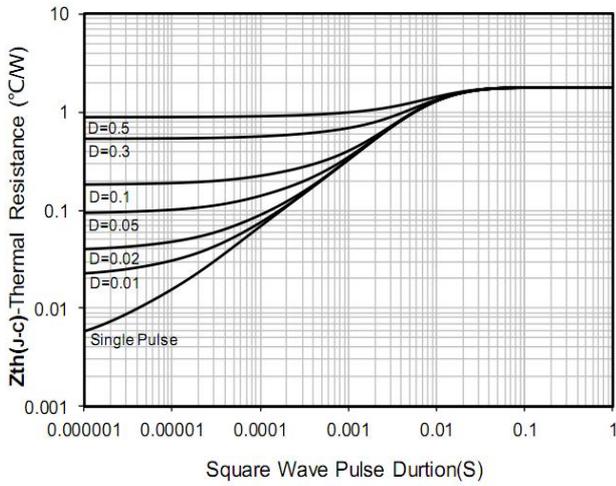


Figure 13. Maximum Transient Thermal Impedance

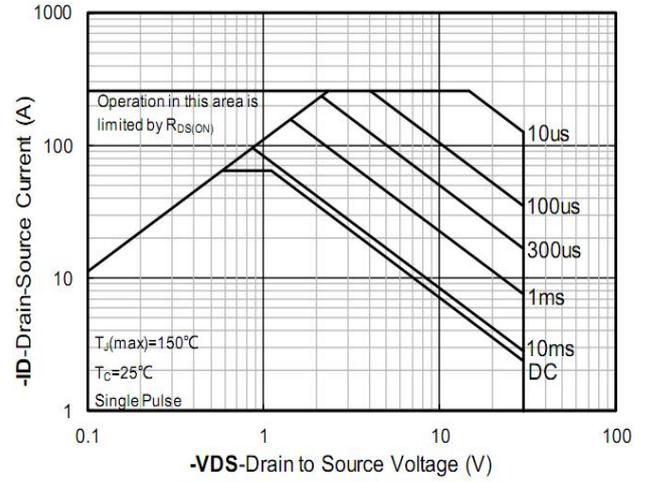
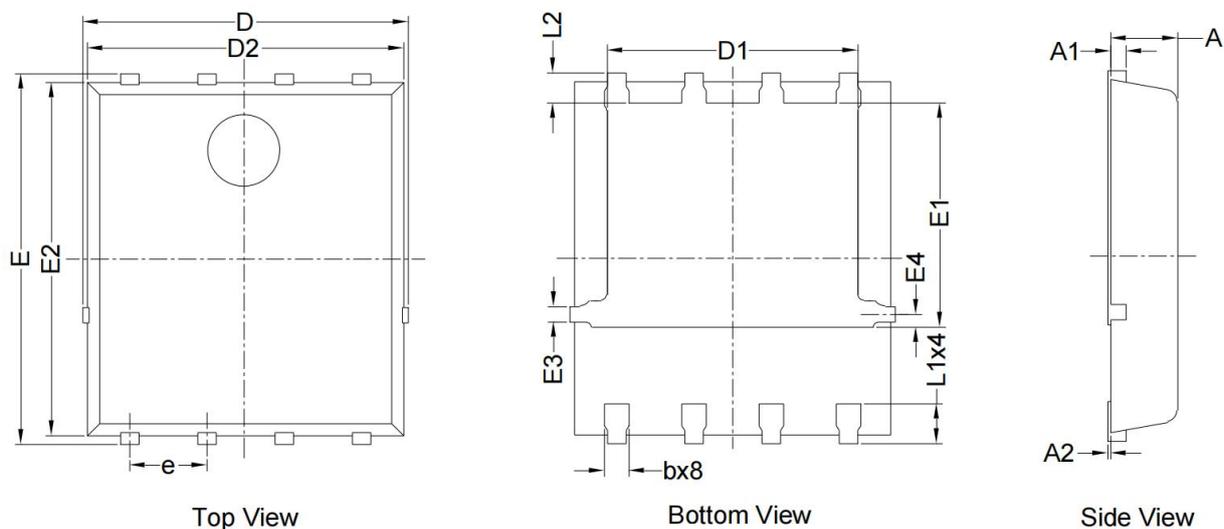


Figure 14. Safe Operation Area

### PDFN5\*6-8L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
D	5.150	5.550	0.203	0.219
E	5.950	6.350	0.234	0.250
A	1.000	1.200	0.039	0.047
A1	0.254 BSC.		0.010 BSC.	
A2	0.000	0.100	0.000	0.004
D1	3.920	4.320	0.154	0.170
E1	3.520	3.920	0.139	0.154
D2	5.000	5.400	0.197	0.213
E2	5.660	6.060	0.223	0.239
E3	0.254 REF.		0.010 REF.	
E4	0.210 REF.		0.008 REF.	
L1	0.560	0.760	0.022	0.030
L2	0.500 BSC.		0.020 BSC.	
b	0.310	0.510	0.012	0.020
e	1.270 BSC.		0.050 BSC.	